

Schottky barrier diode

RB461F

●Applications

Low-power rectification

For switching power supply

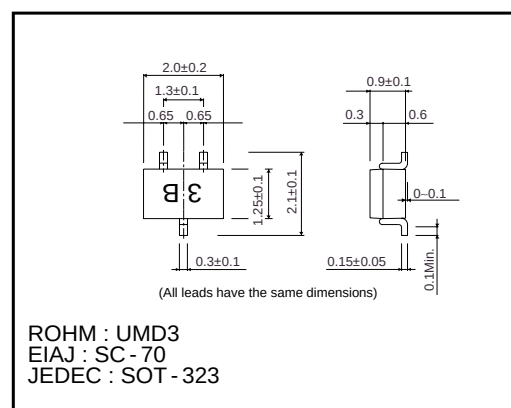
●Features

- 1) Small surface mounting type. (UMD3)
- 2) Ultra low V_F . ($V_F=0.45V$ Typ. at $0.7A$)
- 3) $I_F=0.7A$ guaranteed despite the size.

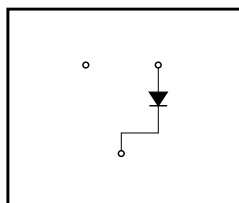
●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Circuit



●Absolute maximum ratings ($T_a=25^{\circ}C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
DC reverse voltage	V_R	20	V
DC forward current	I_F	0.7	A
Peak forward surge current*	I_{FSM}	3	A
Junction temperature	T_j	125	$^{\circ}C$
Storage temperature	T_{stg}	$-40 \sim +125$	$^{\circ}C$

* 60Hz for 1 $\varnothing$

●Electrical characteristics ($T_a=25^{\circ}C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.49	V	$I_F=700mA$
Reverse current	I_R	—	—	200	μA	$V_R=20V$

Note) ESD sensitive product handling required.

Diodes

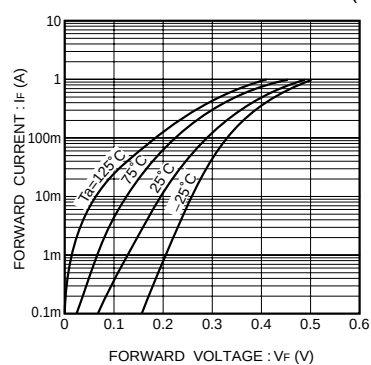
●Electrical characteristic curves ($T_a=25^\circ\text{C}$)

Fig.1 Forward characteristics

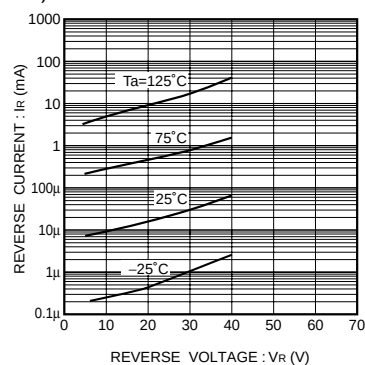


Fig.2 Reverse characteristics

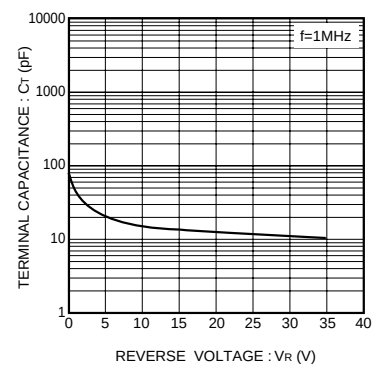


Fig.3 Capacitance between terminals characteristics

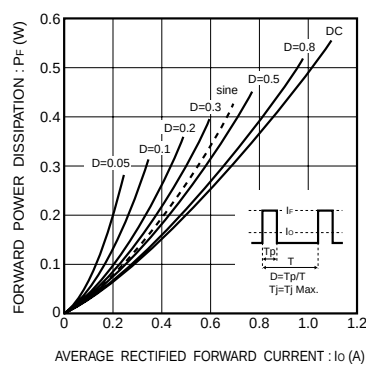
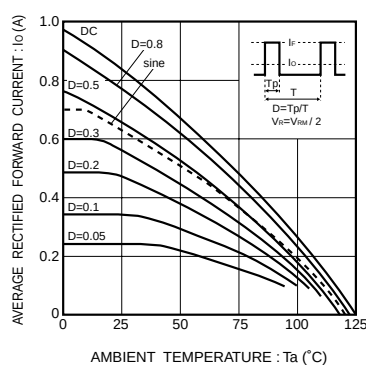


Fig.4 Forward power dissipation characteristics

Fig.5 Derating curve
(when mounted on a glass epoxy PCBs board)